

FEATURES

- **HIGH POWER**
P1dB=38.0 dBm at 13.75 GHz to 14.5 GHz
- **BROAD BAND INTERNALLY MATCHED FET**
- **HERMETICALLY SEALED PACKAGE**
- **HIGH GAIN**
G1dB=6.0 dB at 13.75 GHz to 14.5 GHz

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V f= 13.75 to 14.5GHz	dBm	37.0	38.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	5.0	6.0	—
Drain Current	IDS1		A	—	2.25	2.75
Power Added Efficiency	η_{add}		%	—	23	—
Channel Temperature Rise	ΔT_{ch}	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	80

Recommended gate resistance(Rg) : Rg= 150 Ω (MAX.)

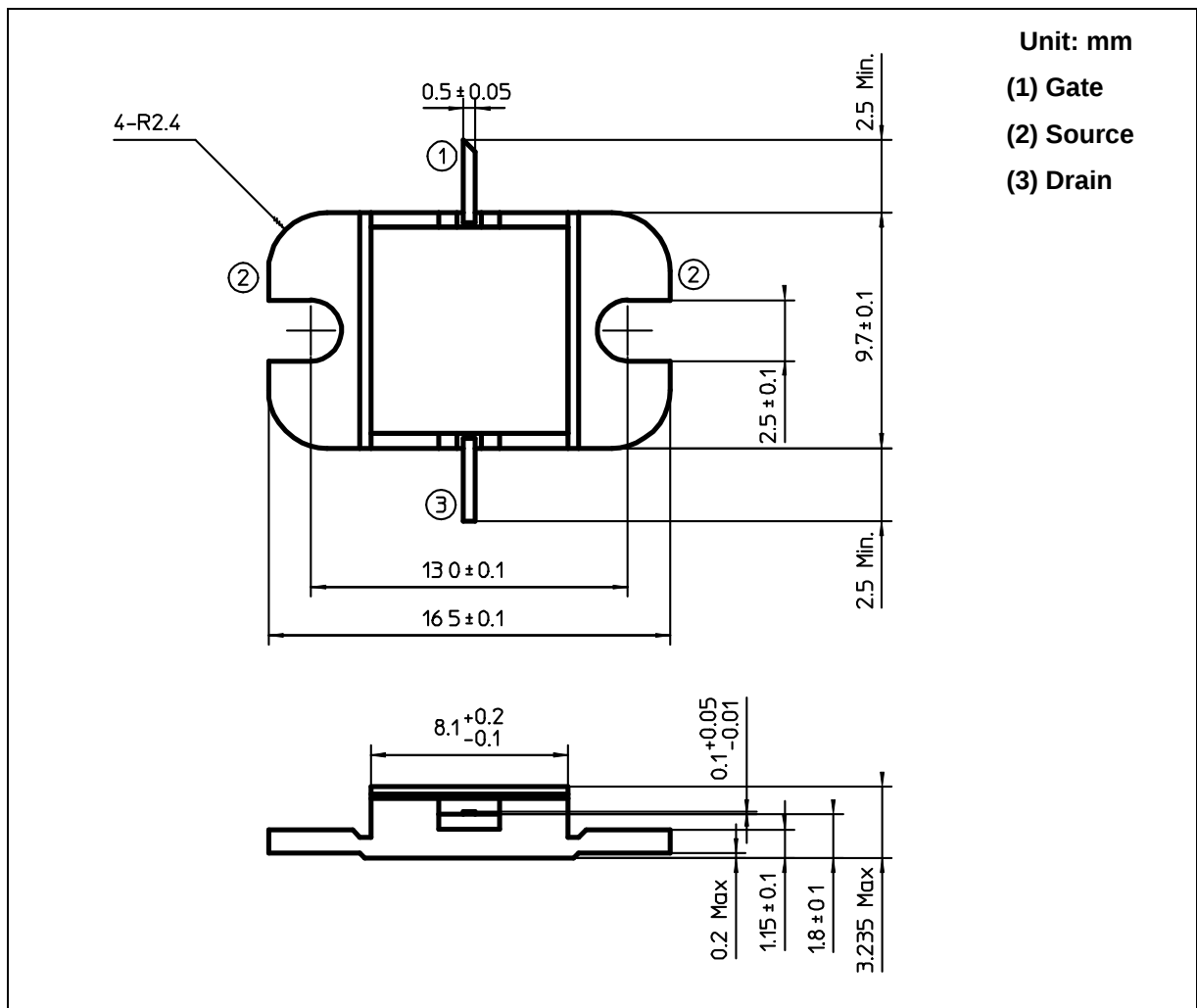
ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.4 A	mS	—	1500	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 72mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	5.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -72 μ A	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	3.0	3.7

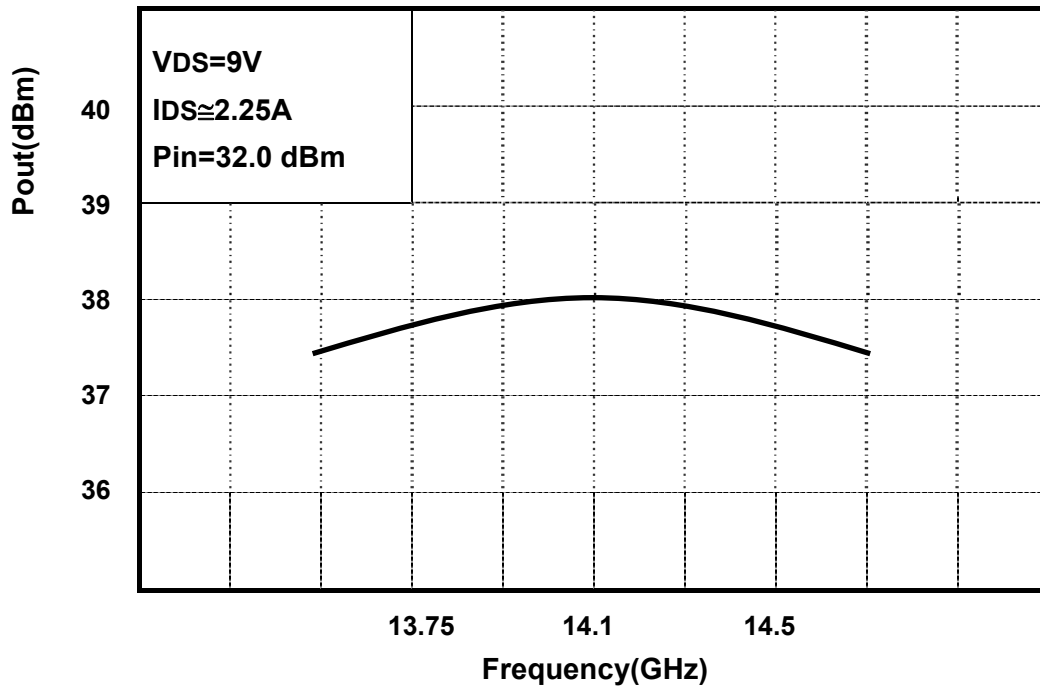
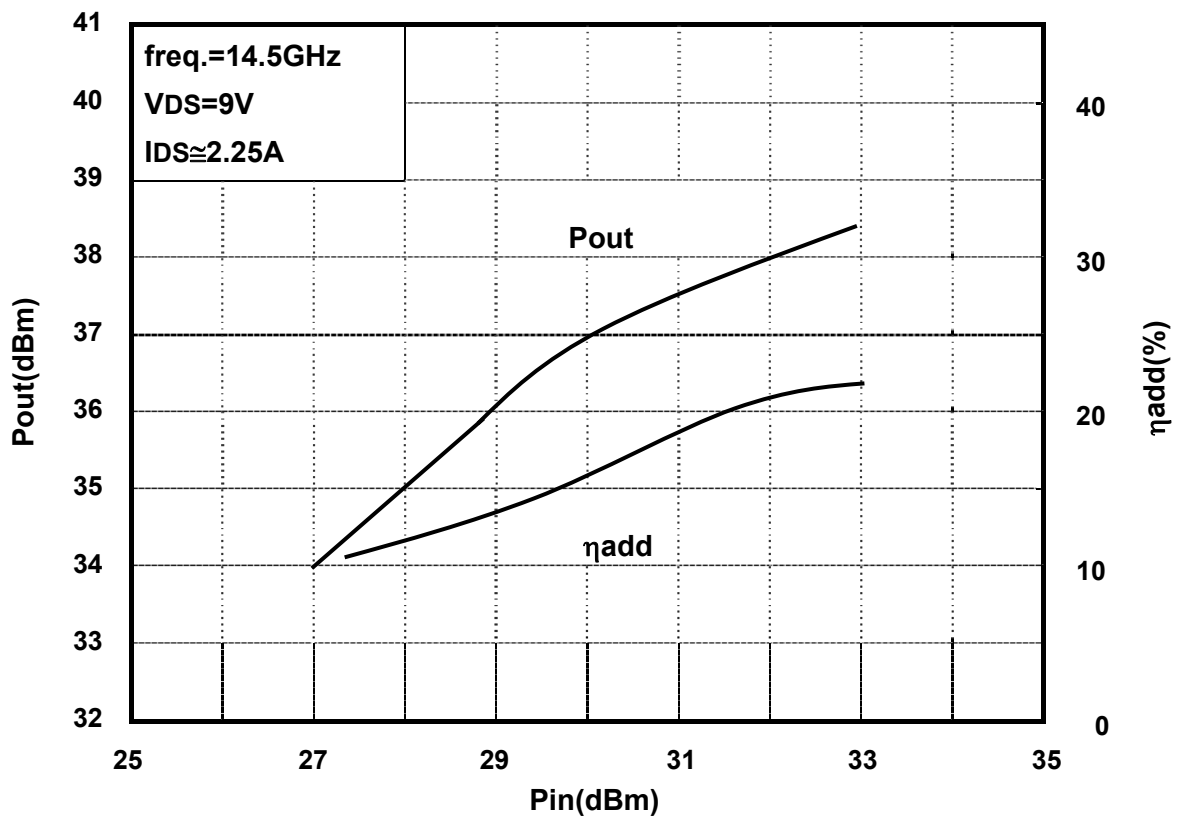
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	5.7
Total Power Dissipation (Tc= 25 °C)	PT	W	40.5
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCE**Output Power (Pout) vs. Frequency****Output Power(Pout) vs. Input Power(Pin)**

Power Dissipation(PT) vs. Case Temperature(Tc)